

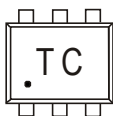
Plastic-Encapsulate Diodes

SWITCHING DIODE

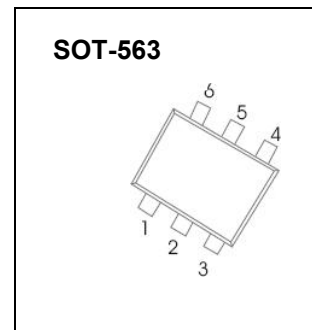
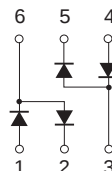
FEATURES

- Fast Switching Speed
- Ultra-Small Surface Mount Package
- For General Purpose Switching Applications
- High Conductance

Marking: TC



Solid point=Pin1 positioning point



Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Peak Repetitive Peak Reverse Voltage	V_{RRM}	75	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_O	150	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	2	A
		1	
Power Dissipation	P_D	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	°C/W
Operating Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	75		V
Reverse voltage leakage current	I_R	$V_R=75V$ $V_R=20V$		2.5 0.030	μA
Forward voltage	V_F	$I_F=1mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$		715 855 1000 1250	mV
Junction capacitance	C_T	$V_R=0, f=1MHz$		2	pF
Revers recovery time	t_{rr}	$I_F=I_R=10mA, I_{rr}=0.1 \times I_R,$ $R_L=100\Omega$		4	ns

Typical Characteristics

